

WHAT IS CLAIMED IS:

1. A semiconductor device, comprising:
 - a silicon oxide film provided over an underlying layer;
 - 5 a fuse line buried in said silicon oxide film, said fuse line forming a fuse;
 - a metal interconnect line buried in said silicon oxide film and said underlying layer to surround said fuse line, said metal interconnect line constituting a shield ring; and
 - a protective film provided on said silicon oxide film, said protective film having resistance to humidity,
 - 10 wherein an opening is created in said protective film which is defined over said fuse line, whereby said silicon oxide film is exposed, and
 - wherein said protective film is in part directly connected to an upper surface of said metal interconnect line without holding said silicon oxide film therebetween.
- 15 2. The semiconductor device according to claim 1, further comprising:
 - an electrode pad provided in an opening which is created in said silicon oxide film and said protective film,
 - wherein said protective film in part covers a side surface of said opening created in said silicon oxide film, to make direct connection to said electrode pad.
- 20 3. The semiconductor device according to claim 1, further comprising:
 - a silicon nitride film provided between said underlying layer and said silicon oxide film.
- 25 4. The semiconductor device according to claim 1,

wherein said protective film is a silicon nitride film.

5. The semiconductor device according to claim 1,

wherein said protective film is a composite of a silicon nitride film and a silicon

5 oxide film, and

wherein said silicon nitride film forming said composite is at least 50 nm or more in thickness.

6. The semiconductor device according to claim 1,

10 wherein said protective film is a polyimide film.